

KS54AHCT
KS74AHCT

139

Dual 1-of-4 Decoders/Demultiplexers

T-67-21-55

FEATURES

- Designed specifically for high-speed memory decoders and data transmission systems
- Incorporates 2 enable inputs to simplify cascading and/or data reception
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5 \text{ V}$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74AHCT: -40°C to $+85^{\circ}\text{C}$
KS54AHCT: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

DESCRIPTION

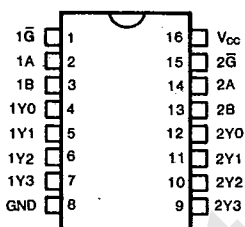
These devices are designed to be used in high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, these decoders can be used to minimize the effects of system decoding. When used with high-speed memories utilizing a fast-enable circuit, the delay times of these decoders and the enable time of the memory are usually less than the typical access time of the memory, this means that the effective system delay introduced by the decoder is negligible.

The '139 consists of two individual two-line to four-line decoders in a single package. The active-low enable input can be used as a data line in demultiplexing applications.

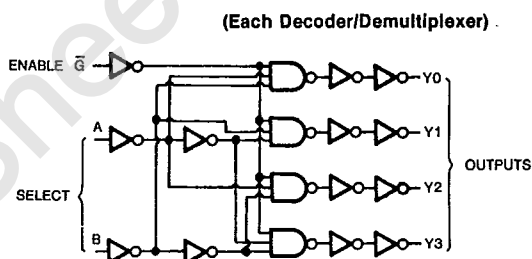
These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

PIN CONFIGURATION



LOGIC DIAGRAM



FUNCTION TABLE

Inputs			Outputs			
Enable G	Select B	A	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L



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KS54AHCT 139
KS74AHCT**Dual 1-of-4 Decoders/Demultiplexers****Absolute Maximum Ratings***

Supply Voltage Range V_{CC} -0.5V to +7V
DC Input Diode Current, I_{IK}
($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
DC Output Diode Current, I_{OK}
($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
Continuous Output Current Per Pin, I_O
($-0.5V < V_O < V_{CC} + 0.5V$) ± 35 mA
Continuous Current Through
 V_{CC} or GND pins ± 125 mA
Storage Temperature Range, T_{stg} -65°C to +150°C
Power Dissipation Per Package, P_d † 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C
Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
DC Input & Output Voltages*, V_{IN} , V_{OUT} ... 0V to V_{CC}
Operating Temperature
Range KS74AHCT: -40°C to +85°C
KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

DC ELECTRICAL CHARACTERISTICS (V _{CC} =5V ± 10% Unless Otherwise Specified)							
Characteristic	Symbol	Test Conditions	T _a = 25°C	KS74AHCT		KS54AHCT	Unit
				T _a = -40°C to +85°C	T _a = -55°C to +125°C		
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V _{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V _{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL} I _O =-20μA I _O =-4mA	V _{CC} 4.2	V _{CC} -0.1 3.98	V _{CC} -0.1 3.84	V _{CC} -0.1 3.7	V
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL} I _O =20μA I _O =4mA I _O =8mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I =2.4V other inputs: at V _{CC} or GND I _{OUT} =0μA		2.7	2.9	3.0	mA



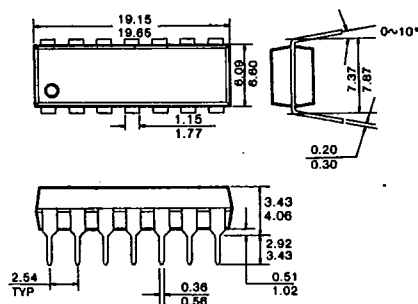
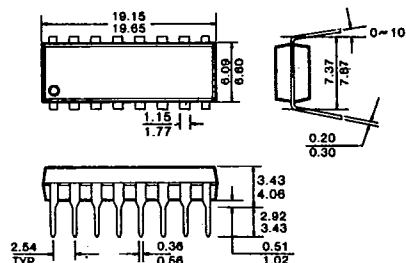
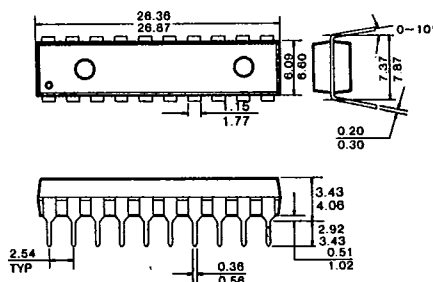
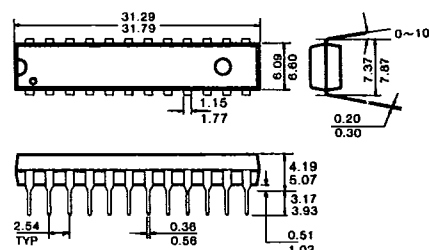
KS54AHCT
KS74AHCT **139****Dual 1-of-4 Decoders/Demultiplexers****AC ELECTRICAL CHARACTERISTICS** (Input $t_r, t_f \leq 2$ ns), AHCT139

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay, A or B to Y	t_{PLH}	$C_L = 50\text{pF}$	11		17		20	ns
	t_{PHL}		11		17		20	
Propagation Delay, $\bar{G}$ to any Y	t_{PLH}		11		18		21	ns
	t_{PHL}		11		18		21	
Input Capacitance	C_{IN}		5					pF
Power Dissipation Capacitance*	C_{PD}		50					pF

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.



PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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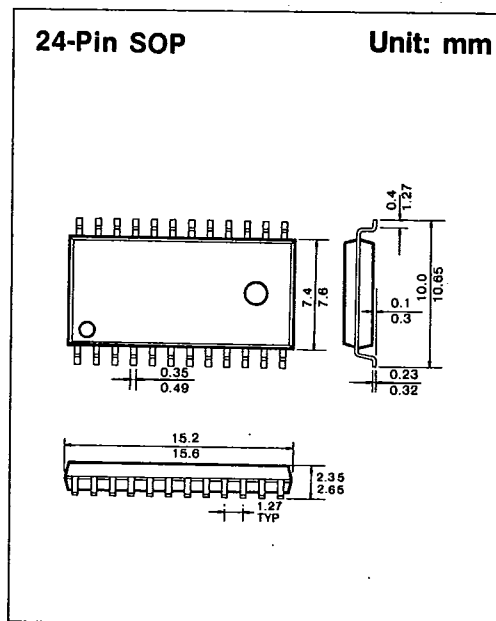
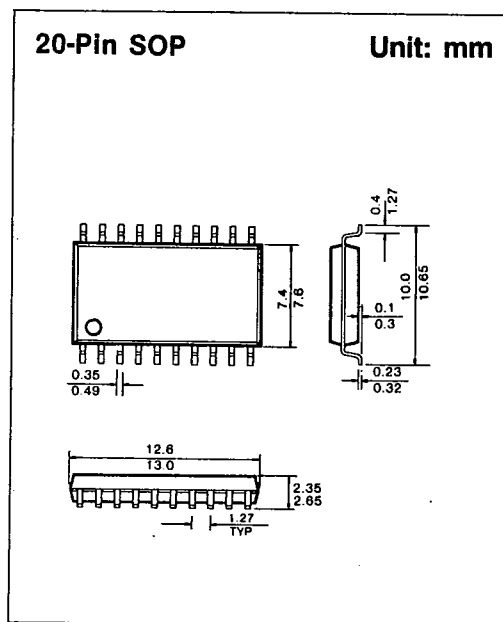
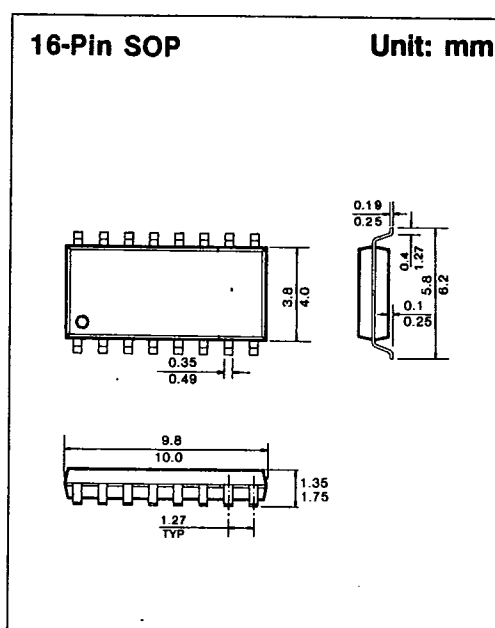
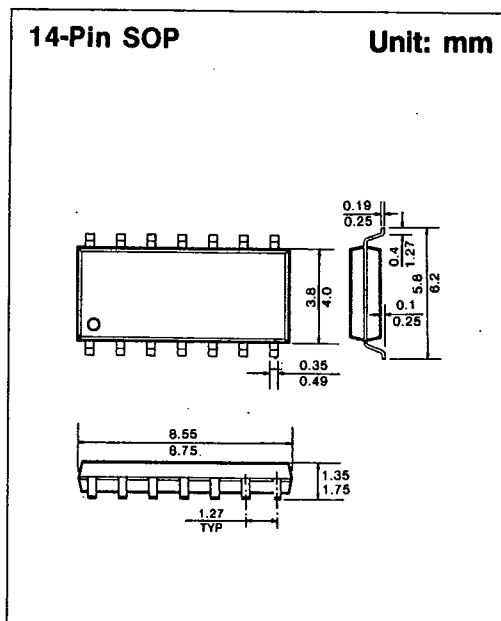
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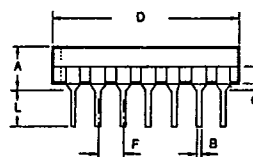
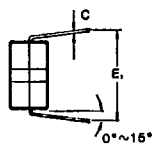
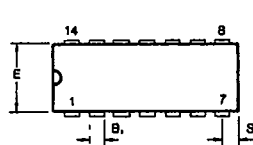
PACKAGE DIMENSIONS

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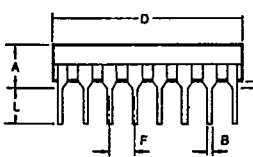
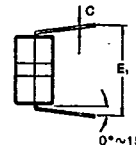
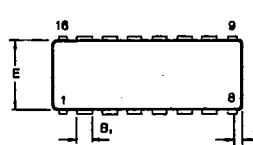


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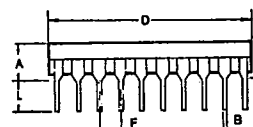
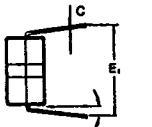
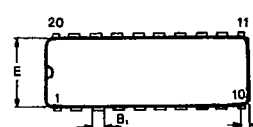
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2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

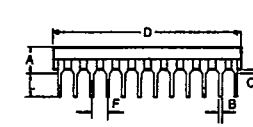
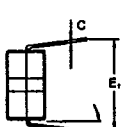
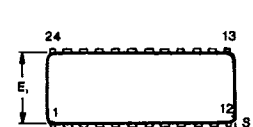
DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93



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783